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The rev A is being issued to update the ZVEI ID section.

PCN Number:	20260629004.2A	PCN Issued	August 17, 2026
Qualification of RFAB using qualified Process Technology, Design, Datasheet, Test site, and BOM options for select devices		Sample request deadline:	August 30, 2026
		Estimated 1st ship date:	December 28, 2026
*Sample requests received after August 30, 2026 will not be supported.			

Change Type(s)	Assembly Site Assembly Process Assembly Material Packing/Shipping/Labeling Design Data Sheet/Electrical Specification Test Site Wafer Fab Site Wafer Fab Material Wafer Fab Process
ZVEI ID	SEM-PA-18, SEM-PA-08, SEM-PA-11, SEM-PA-07, SEM-DE-01, SEM-DE-02, SEM-DE-03, SEM-TF-01, SEM-PW-13, SEM-PW-02, SEM-PW-09, SEM-DS-01, SEM-DS-02, SEM-PS-04, SEM-PS-02

PCN Details

Description of Change:

Texas Instruments is pleased to announce the addition of RFAB using the LBC9 qualified process technology, Design, Datasheet, Test site, and assembly BOM options for the devices listed below.

Current Fab Site			Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
SFAB	J11	150mm	RFAB	LBC9	300mm

The die was also changed as a result of the process change.

Construction Differences are as follows:

	Current	Additional
Assembly Site	MLA	CLARK-AT
Bond wire composition, diameter	Au, 0.96mil	Cu, 0.8mil
Mount Compound	4207123	4225839
Mold Compound	4208625	4222198
MSL	LEVEL2-260C	LEVEL1-260C

	Current	Additional Site
Test Site	MLA	Clark-AT

The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history shown below. The links to the

revised datasheets are available in the table below.



LP2951-Q1

SLVSAW6J – JUNE 2011 – REVISED JUNE 2026

Changes from Revision I (November 2025) to Revision J (June 2026)	Page
• Updated output range for adjustable configuration.....	1
• Updated the output range for adjustable configuration	1
• Updated thermal information for DRG package.....	5
• Added Electrical limits for LP295X-XXADJ variant	5
• Updated output range for Adjustable config and added details about V_{REF}	19
• Updated details about I_{FB} current and updated equation about the V_{OUT} voltage.....	26
• Updated details about FEEDBACK pin and V_{FB} , voltage on FEEDBACK pin.....	26
• Added nomenclature details about LP2951xxADJ device.....	31

Product Folder	Current Datasheet Number	New Datasheet Number	Link to full datasheet
LP2951-Q1	SLVSAW6I	SLVSAW6J	http://www.ti.com/product/LP2951-Q1

Qual details are provided in the Qual Data Section.

Reason for Change:	These changes are part of our multiyear plan to transition products from our 200-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.
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Anticipated impact on Form, Fit, Function, Quality or Reliability:	• These devices include new die with schematic or behavior changes. • There are changes in the electrical tables. • Device quality has been impacted. • Review updated datasheets and/or the Standard Data Packet for more details on the changes. Evaluating samples is encouraged.
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Impact on Environmental Ratings	Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.			
	RoHS	REACH	Green Status	IEC 62474
	☒ No Change	☒ No Change	☒ No Change	☒ No Change

Changes to product identification resulting from this PCN:	Fab Site Information												
	<table><tr><td>Chip Site</td><td>Chip Site Origin Code (20L)</td><td>Chip Site Country Code (21L)</td><td>Chip Site City</td></tr><tr><td>SFAB</td><td>SHE</td><td>USA</td><td>SHERMAN</td></tr><tr><td>RFAB</td><td>RFB</td><td>USA</td><td>Richardson</td></tr></table>	Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City	SFAB	SHE	USA	SHERMAN	RFAB	RFB	USA	Richardson
	Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City									
	SFAB	SHE	USA	SHERMAN									
RFAB	RFB	USA	Richardson										

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>LP2951-50QDRGRM3Q1</u>	Qual Device: <u>LP2951-33QDRGRM3Q1</u>
Test Group A - Accelerated Environment Stress Tests									
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/786/0	-
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	-
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	-
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/233/0	-
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/233/0	-
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/238/0	-
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/233/0	-
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/145/0	-
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0	-
Test Group C - Package Assembly Integrity Tests									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device LP2951-50QDRGRM3Q1 is qualified at MSL1 260C
- Qual Device LP2951-33QDRGRM3Q1 is qualified at MSL1 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-NPD-2503-096

Product Attributes

Attributes	Qual Device: <u>LP2951-50QDRGRM3Q1</u>	Qual Device: <u>LP2951-33QDRGRM3Q1</u>	QBS Process Reference: <u>BQ79600PWRQ1</u>	QBS Process, Product Reference: <u>LP2951-50QDRGRQ1M3</u>	QBS Product Reference: <u>LP2951-50QDRGRQ1M3</u>
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Power Management	Power Management	Power Management
Wafer Fab Supplier	RFAB	RFAB	RFAB	RFAB	RFAB
Assembly Site	CLARK-AT	CLARK-AT	MLA	FMX	CDAT
Package Group	QFN	QFN	TSSOP	SOIC	QFN
Package Designator	DRG	DRG	PW	D	DRG
Pin Count	8	8	16	8	8

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device LP2951-50QDRGRM3Q1 is qualified at MSL1 260C
- Qual Device LP2951-33QDRGRM3Q1 is qualified at MSL1 260C

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LP2951-50QDRGRM3Q1	Qual Device: LP2951-33QDRGRM3Q1	QBS Process Reference: BQ79600PWRQ1	QBS Process, Product Reference: LP2951-50QDRQ1M3	QBS Product Reference: LP2951-50QDRGRQ1M3
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/All0	-	-	-	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	-	-	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	3/231/0	-	-	-	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	-	-	-	-
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-	-	-	-
TC-SAM	A4	-	3	3	Post TC SAM	<50% delamination	-	1/12/0	-	-	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	-	-	-	-
Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	-	3/231/0	1/77/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	-
EDR	B3	AEC Q100-005	1	77	NVM Endurance, Data Retention, and Op Life	Per QSS-009-018	1 Step	-	-	3/231/0	-	-

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: LP2951-50QDRGRM3Q1	Qual Device: LP2951-33QDRGRM3Q1	QBS Process Reference: BQ79600PWRQ1	QBS Process, Product Reference: LP2951-50QDRQ1M3	QBS Product Reference: LP2951-50QDRGRQ1M3
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-	-	-	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	-	-	-	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	-	-	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	3/30/0	-	-	-	3/30/0
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDb	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												

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ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	-	-	-	1/3/0	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	-	-	-	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	3	Latch-Up	Per AEC Q100-004	-	-	-	-	1/3/0	1/3/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	-	2/60/0	3/90/0	1/30/0

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TI Qualification ID: R-NPD-2503-096

In performing change qualifications, Texas Instruments follows integrated circuit industry standards in performing defect mechanism analysis and failure mechanism-based accelerated environmental testing to ensure wafer fab process, assembly process and product quality and reliability. As encouraged by these standards, TI uses both product-specific and generic (family) data in qualifying its changes. For devices to be categorized as a 'product qualification family' for generic data purposes, they must share similar product, wafer fab process and assembly process elements. The applicability of generic data (also known at TI as Qualification by Similarity (QBS)) is determined by the Reliability Engineering function following these industry standards. Generic data is shown in the qualification report in columns titled "QBS Process" (for wafer fab process), "QBS Package" (for assembly process) and "QBS Product" (for product family).

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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